

Schottky Barrier Diode

Features

1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		LL60	V_{RRM}	40	V
		LL60P	V_{RRM}	45	V
Peak forward surge current	$t_p \leq 1 \text{ s}$	LL60	I_{FSM}	150	mA
		LL60P	I_{FSM}	500	mA
Forward continuous current	$T_a=25^{\circ}\text{C}$	LL60	I_F	30	mA
		LL60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	$^{\circ}\text{C}$

Maximum Thermal Resistance

$T_j=25^{\circ}\text{C}$

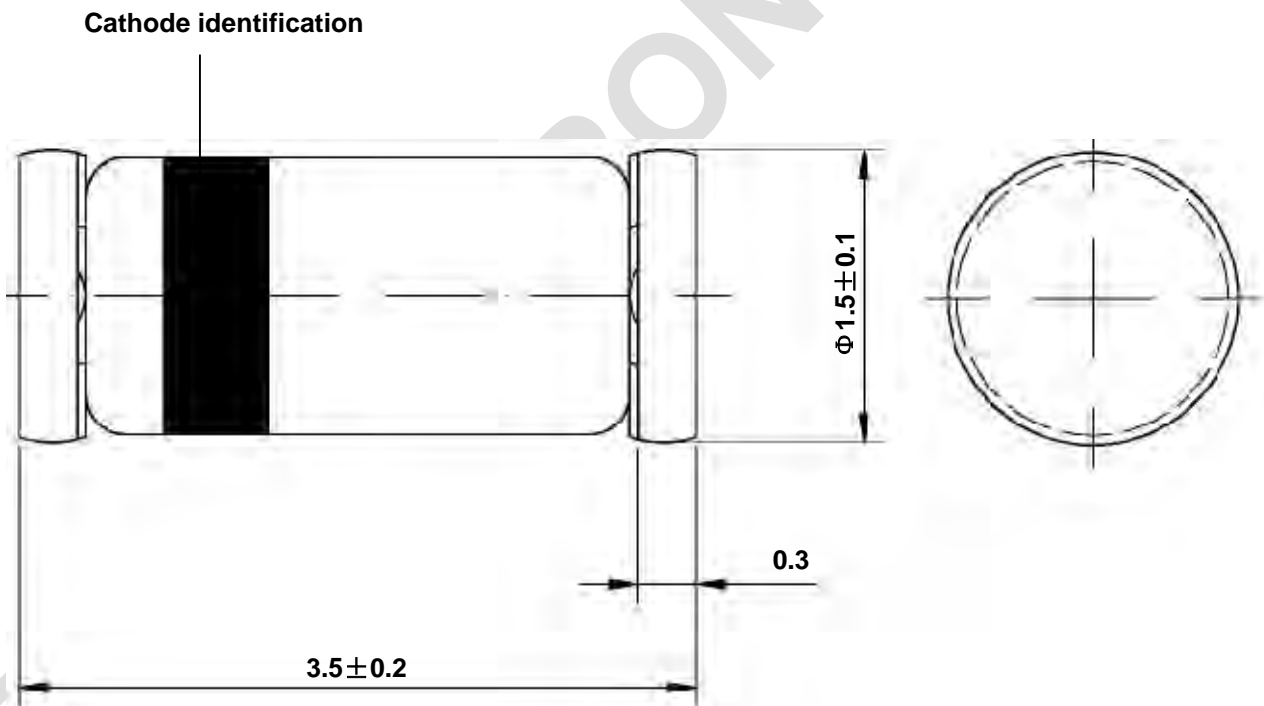
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm × 50mm × 1.6mm	R_{thJA}	250	K/W

Electrical Characteristics

T_j=25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =1mA	LL60	V _F		0.32	0.5	V
		LL60P	V _F		0.24	0.5	V
	I _F =30mA	LL60	V _F		0.65	1.0	V
		LL60P	V _F		0.65	1.0	V
Reverse current	V _R =15V	LL60	I _R		0.1	0.5	μ A
		LL60P	I _R		0.5	1.0	μ A
Junction capacitance	V _R =1V, f=1MHz	LL60	C _J		2.0		pF
	V _R =10V, f=1MHz	LL60P	C _J		6.0		pF
Reverse recovery time	I _F =I _R =1mA I _{tr} =1mA R _C =100		t _{rr}			1.0	ns

Dimensions in mm



Glass Case
Mini Melf / SOD 80
JEDEC DO 213 AA